

# New Jersey Semi-Conductor Products, Inc.

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## 1N5829, 1N5830 1N5831

### Designers Data Sheet

#### HOT CARRIER POWER RECTIFIERS

... employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Extremely Low  $v_f$
- Low Power Loss/High Efficiency
- Low Stored Charge, Majority Carrier Conduction
- High Surge Capacity
- TX Version Available

#### Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

#### \*MAXIMUM RATINGS

| Rating  | Symbol          | 1N 5829           | 1N 5830 | 1N 5831 | Unit             |
|---|-----------------|-------------------|---------|---------|------------------|
| Peak Repetitive Reverse Voltage   | $V_{RRM}$       |                   |         |         |                  |
| Working Peak Reverse Voltage  | $V_{RWM}$       | 20                | 30      | 40      | Volts            |
| DC Blocking Voltage   | $V_R$           |                   |         |         |                  |
| Non-Repetitive Peak Reverse Voltage   | $V_{RSM}$       | 24                | 36      | 48      | Volts            |
| Average Rectified Forward Current<br>$V_f(\text{requ}) \leq 0.2 V_R (\text{dc}), T_C = 85^\circ\text{C}$    | $I_O$           | 25                |         |         | Amp              |
| Ambient Temperature<br>Rated $V_R$ (dc), $P_f(AV) = 0$ ,<br>$R_{\theta JA} = 3.5^\circ\text{C}/\text{W}$    | $T_A$           | 90                | 85      | 80      | $^\circ\text{C}$ |
| Non-Repetitive Peak Surge Current<br>(Surge applied at rated load conditions, halfwave, single phase 60 Hz) | $I_{FSM}$       | 800 (for 1 cycle) |         |         | Amp              |
| Operating and Storage Junction Temperature Range (Reverse voltage applied)                                  | $T_J, T_{S(t)}$ | -65 to +125       |         |         | $^\circ\text{C}$ |
| Peak Operating Junction Temperature (Forward Current Applied)   | $T_J(pk)$       | 150               |         |         | $^\circ\text{C}$ |

#### \*THERMAL CHARACTERISTICS

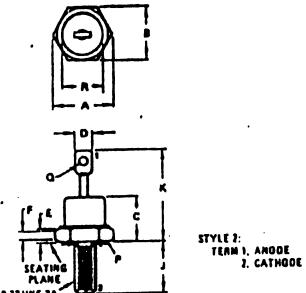
| Characteristic                       | Symbol          | Max  | Unit                      |
|--------------------------------------|-----------------|------|---------------------------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.75 | $^\circ\text{C}/\text{W}$ |

#### \*ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic  | Symbol | 1N 5829                 | 1N 5830                 | 1N 5831                 | Unit  |
|---|--------|-------------------------|-------------------------|-------------------------|-------|
| Maximum Instantaneous Forward Voltage (1)<br>( $i_F = 10 \text{ Amp}$ )<br>( $i_F = 25 \text{ Amp}$ )<br>( $i_F = 78.5 \text{ Amp}$ ) | $v_F$  | 0.360<br>0.440<br>0.720 | 0.370<br>0.460<br>0.770 | 0.380<br>0.480<br>0.820 | Volts |
| Maximum Instantaneous Reverse Current @ Rated dc Voltage (1)<br>( $T_C = 100^\circ\text{C}$ )   | $i_R$  | 20<br>150               | 20<br>150               | 20<br>150               | mA    |

#### SCHOTTKY BARRIER RECTIFIERS

15 AMPERE  
20,30,40 VOLTS



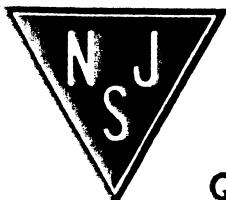
| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MILS        | MMS   | MM     | INCH  |
| A   | 11.94       | 11.91 | 0.470  | 0.018 |
| B   | 10.77       | 10.74 | 0.424  | 0.017 |
| C   | -           | 10.20 | -      | 0.400 |
| D   | -           | 5.93  | -      | 0.230 |
| E   | 1.81        | 1.78  | 0.070  | 0.003 |
| F   | 1.37        | 1.34  | 0.053  | 0.002 |
| G   | 10.77       | 11.01 | 0.422  | 0.017 |
| H   | -           | 20.32 | -      | 0.800 |
| I   | 4.14        | 4.00  | 0.160  | 0.006 |
| J   | 1.52        | 1.48  | 0.058  | 0.002 |
| K   | -           | 10.77 | -      | 0.420 |

All JEDEC dimensions and notes apply

DO-4

#### MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed  
FINISH: All external surfaces corrosion resistant and terminal leads are readily solderable.  
POLARITY: Cathode to Case  
MOUNTING POSITION: Any  
STUD TORQUE: 15 in. lb. max



Quality Semi-Conductors